

## General Description

Renesas SLG7RN45323 is a low power and small form device. The SoC is housed in a 1.6mm x 1.6mm STQFN package which is optimal for using with small devices.

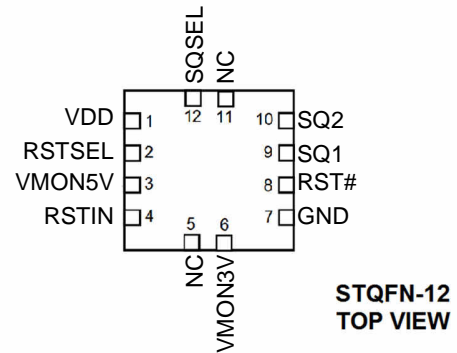
## Features

- Low Power Consumption
- Pb - Free / RoHS Compliant
- Halogen - Free
- STQFN - 12 Package

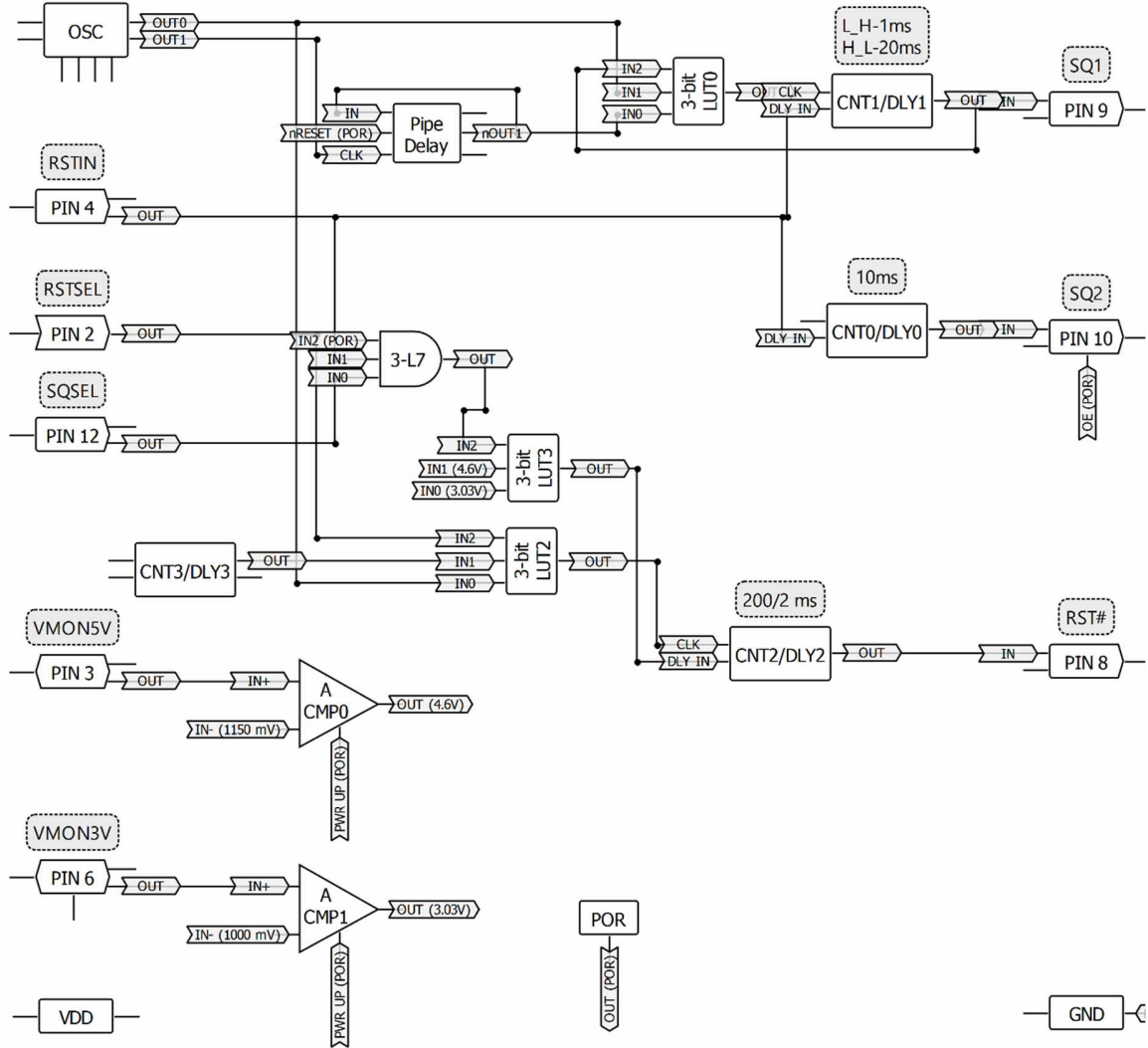
## Output Summary

1 Output - Open Drain NMOS 1X  
 2 Outputs - Push Pull 1X

## Pin Configuration



Block Diagram



**Pin Configuration**

Pin #	Pin Name	Type	Pin Description	Internal Resistor
1	VDD	PWR	Supply Voltage	--
2	RSTSEL	Digital Input	Digital Input without Schmitt trigger	1MΩ pulldown
3	VMON5V	Analog Input/Output	Analog Input/Output	floating
4	RSTIN	Digital Input	Digital Input with Schmitt trigger	10kΩ pullup
5	NC	--	Keep Floating or Connect to GND	--
6	VMON3V	Analog Input/Output	Analog Input/Output	floating
7	GND	GND	Ground	--
8	RST#	Digital Output	Open Drain NMOS 1X	floating
9	SQ1	Digital Output	Push Pull 1X	floating
10	SQ2	Digital Output	Push Pull 1X	floating
11	NC	--	Keep Floating or Connect to GND	--
12	SQSEL	Digital Input	Digital Input without Schmitt trigger	1MΩ pulldown

**Ordering Information**

Part Number	Package Type
SLG7RN45323V	STQFN-12 – Tape and Reel (3k units)

**Absolute Maximum Conditions**

Parameter	Min.	Max.	Unit
Supply Voltage on VDD relative to GND	-0.5	7	V
DC Input Voltage	GND - 0.5V	VDD + 0.5V	V
Maximum Average or DC Current (Through pin)	Push-Pull 1x	--	mA
	OD 1x	--	
Current at Input Pin	-1.0	1.0	mA
Input leakage (Absolute Value)	--	1000	nA
Storage Temperature Range	-65	150	°C
Junction Temperature	--	150	°C
ESD Protection (Human Body Model)	2000	--	V
ESD Protection (Charged Device Model)	1000	--	V
Moisture Sensitivity Level	1		

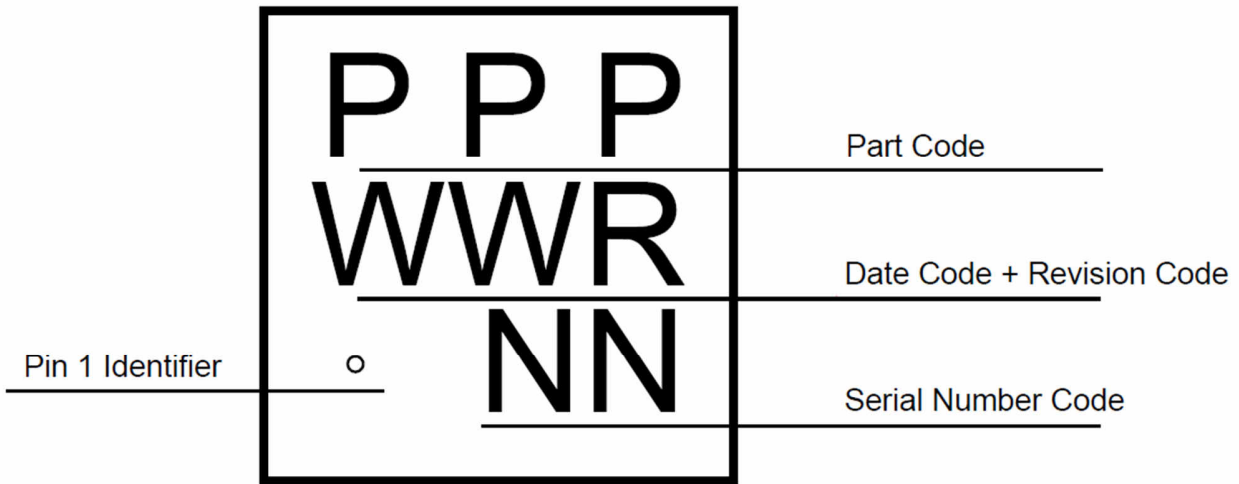
**Electrical Characteristics**

Symbol	Parameter	Condition/Note	Min.	Typ.	Max.	Unit
V <sub>DD</sub>	Supply Voltage		1.71	5	5.5	V
T <sub>A</sub>	Operating Temperature		-40	25	85	°C
C <sub>VDD</sub>	Capacitor Value at VDD		--	0.1	--	μF
C <sub>IN</sub>	Input Capacitance		--	4	--	pF
I <sub>Q</sub>	Quiescent Current	Static inputs and floating outputs	--	76	--	μA
V <sub>O</sub>	Maximal Voltage Applied to any PIN in High-Impedance State		--	--	VDD	V
I <sub>VDD</sub>	Maximum Average or DC Current Through VDD Pin (Per chip side, see Note 2)	T <sub>J</sub> = 85°C	--	--	73	mA
I <sub>VDD</sub>	Maximum Average or DC Current Through VDD Pin (Per chip side, see Note 2)	T <sub>J</sub> = 110°C	--	--	35	mA
I <sub>GND</sub>	Maximum Average or DC Current Through GND Pin (Per chip side, see Note 2)	T <sub>J</sub> = 85°C	--	--	92	mA
I <sub>GND</sub>	Maximum Average or DC Current Through GND Pin (Per chip side, see Note 2)	T <sub>J</sub> = 110°C	--	--	44	mA
V <sub>IH</sub>	HIGH-Level Input Voltage	Logic Input at VDD=1.8V	1.100	--	VDD	V
		Logic Input at VDD=3.3V	1.780	--	VDD	V
		Logic Input at VDD=5.0V	2.640	--	VDD	V
		Logic Input with Schmitt Trigger at VDD=1.8V	1.270	--	VDD	V
		Logic Input with Schmitt Trigger at VDD=3.3V	2.130	--	VDD	V
		Logic Input with Schmitt Trigger at VDD=5.0V	3.160	--	VDD	V
V <sub>IL</sub>	LOW-Level Input Voltage	Logic Input at VDD=1.8V	0	--	0.690	V
		Logic Input at VDD=3.3V	0	--	1.210	V
		Logic Input at VDD=5.0V	0	--	1.840	V

		Logic Input with Schmitt Trigger at VDD=1.8V	0	--	0.440	V
		Logic Input with Schmitt Trigger at VDD=3.3V	0	--	0.950	V
		Logic Input with Schmitt Trigger at VDD=5.0V	0	--	1.510	V
V <sub>OH</sub>	HIGH-Level Output Voltage	Push-Pull 1X, Open Drain PMOS 1X, I <sub>OH</sub> =100μA, at VDD=1.8V	1.680	1.790	--	V
		Push-Pull 1X, Open Drain PMOS 1X, I <sub>OH</sub> =3mA, at VDD=3.3V	2.720	3.090	--	V
		Push-Pull 1X, Open Drain PMOS 1X, I <sub>OH</sub> =5mA, at VDD=5.0V	4.170	4.740	--	V
V <sub>OL</sub>	LOW-Level Output Voltage	Push-Pull 1X, I <sub>OL</sub> =100μA, at VDD=1.8V	--	0.020	0.030	V
		Push-Pull 1X, I <sub>OL</sub> =3mA, at VDD=3.3V	--	0.180	0.280	V
		Push-Pull 1X, I <sub>OL</sub> =5mA, at VDD=5.0V	--	0.230	0.330	V
		Open Drain NMOS 1X, I <sub>OL</sub> =100μA, at VDD=1.8V	--	0.010	0.020	V
		Open Drain NMOS 1X, I <sub>OL</sub> =3mA, at VDD=3.3V	--	0.090	0.130	V
		Open Drain NMOS 1X, I <sub>OL</sub> =5mA, at VDD=5.0V	--	0.120	0.160	V
I <sub>OH</sub>	HIGH-Level Output Current (Note 1)	Push-Pull 1X, Open Drain PMOS 1X, V <sub>OH</sub> =VDD-0.2V, at VDD=1.8V	1.000	1.390	--	mA
		Push-Pull 1X, Open Drain PMOS 1X, V <sub>OH</sub> =2.4V, at VDD=3.3V	6.010	10.150	--	mA
		Push-Pull 1X, Open Drain PMOS 1X, V <sub>OH</sub> =2.4V, at VDD=5.0V	21.980	29.001	--	mA
I <sub>OL</sub>	LOW-Level Output Current (Note 1)	Push-Pull 1X, V <sub>OL</sub> =0.15V, at VDD=1.8V	0.760	1.340	--	mA
		Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=3.3V	4.060	6.440	--	mA
		Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=5.0V	6.010	9.730	--	mA
		Open Drain NMOS 1X, V <sub>OL</sub> =0.15V, at VDD=1.8V	1.530	2.670	--	mA
		Open Drain NMOS 1X, V <sub>OL</sub> =0.4V, at VDD=3.3V	8.130	12.410	--	mA
		Open Drain NMOS 1X, V <sub>OL</sub> =0.4V, at VDD=5.0V	11.760	19.460	--	mA
R <sub>PULL_UP</sub>	Internal Pull Up Resistance	Pull up on PIN 4	--	10	--	kΩ
R <sub>PULL_DOWN</sub>	Internal Pull Down Resistance	Pull down on PINs 2, 12	--	1	--	MΩ
T <sub>DLY0</sub>	Delay0 Time	At temperature 25°C	9.22	10	10.69	ms

		At temperature -40 +85°C (Note 3)	8.62	10	12.65	ms
T <sub>CNT3</sub>	Counter3 Period	At temperature 25°C	7.26	7.84	8.35	ms
		At temperature -40 +85°C (Note 3)	6.78	7.84	9.88	ms
V <sub>ACMP0</sub>	Analog Comparator0 Threshold Voltage	Low to High transition, at temperature 25°C	4400	--	4793	mV
		Low to High transition, at temperature -40 +85°C (Note 3)	4250	--	4859	mV
		High to Low transition, at temperature 25°C	4399	--	4792	mV
		High to Low transition, at temperature -40 +85°C (Note 3)	4248	--	4857	mV
V <sub>ACMP1</sub>	Analog Comparator1 Threshold Voltage	Low to High transition, at temperature 25°C	2855	--	3130	mV
		Low to High transition, at temperature -40 +85°C (Note 3)	2763	--	3175	mV
		High to Low transition, at temperature 25°C	2854	--	3129	mV
		High to Low transition, at temperature -40 +85°C (Note 3)	2760	--	3174	mV
T <sub>SU</sub>	Startup Time	From VDD rising past 1.35 V	--	0.31	--	ms
PON <sub>THR</sub>	Power On Threshold	V <sub>DD</sub> Level Required to Start Up the Chip	1.180	1.353	1.516	V
POFF <sub>THR</sub>	Power Off Threshold	V <sub>DD</sub> Level Required to Switch Off the Chip	0.730	0.914	1.103	V
Note: 1. DC or average current through any pin should not exceed value given in Absolute Maximum Conditions. 2. The GreenPAK's power rails are divided in two sides. Pins 2, 3, 4, 5 and 6 are connected to one side, pins 8, 9, 10, 11 and 12 to another. 3. Guaranteed by Design.						

Package Top Marking

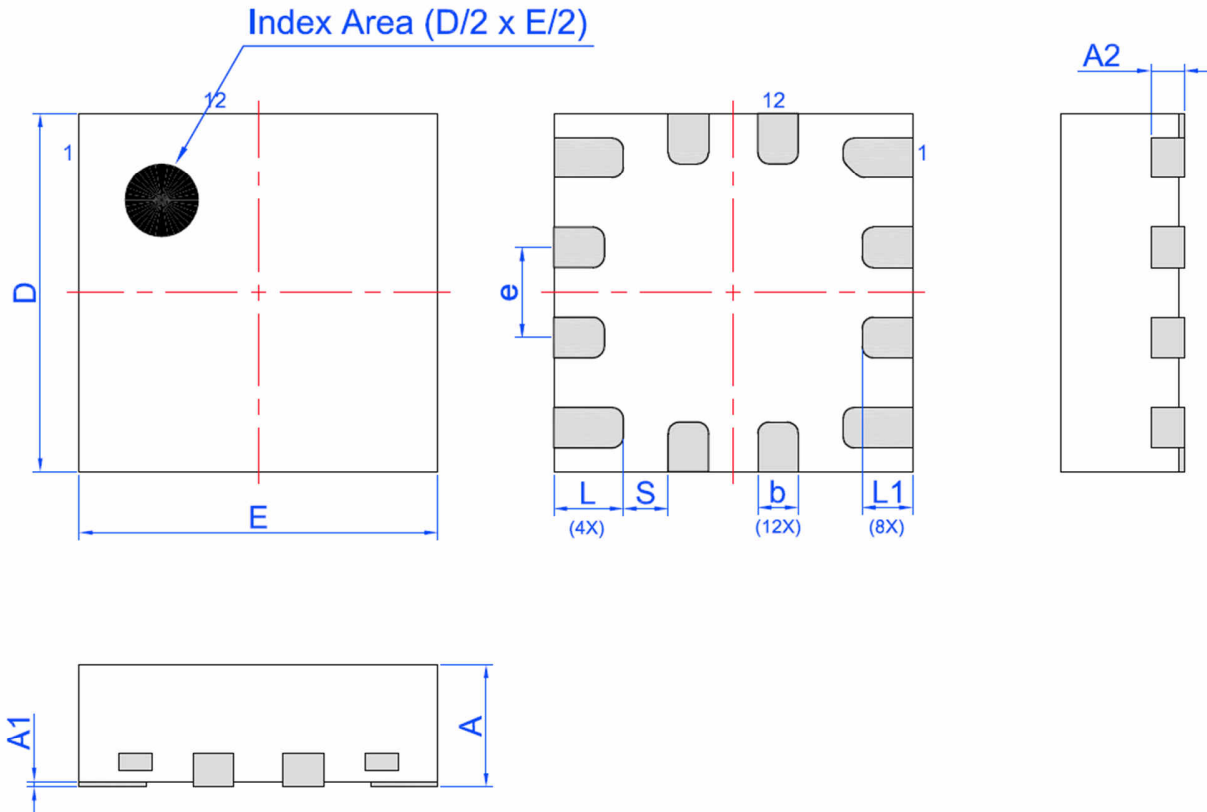


Datasheet Revision	Programming Code Number	Lock Status	Checksum	Part Code	Revision	Date
0.11	001	U	0x85F199C6			07/11/2023

The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.

#### Package Drawing and Dimensions

12 Lead STQFN FCA Package 1.6 x 1.6 mm



Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
A	0.50	0.55	0.60	D	1.55	1.60	1.65
A1	0.005	-	0.060	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.26	0.31	0.36
b	0.13	0.18	0.23	L1	0.175	0.225	0.275
e	0.40 BSC			S	0.2 REF		

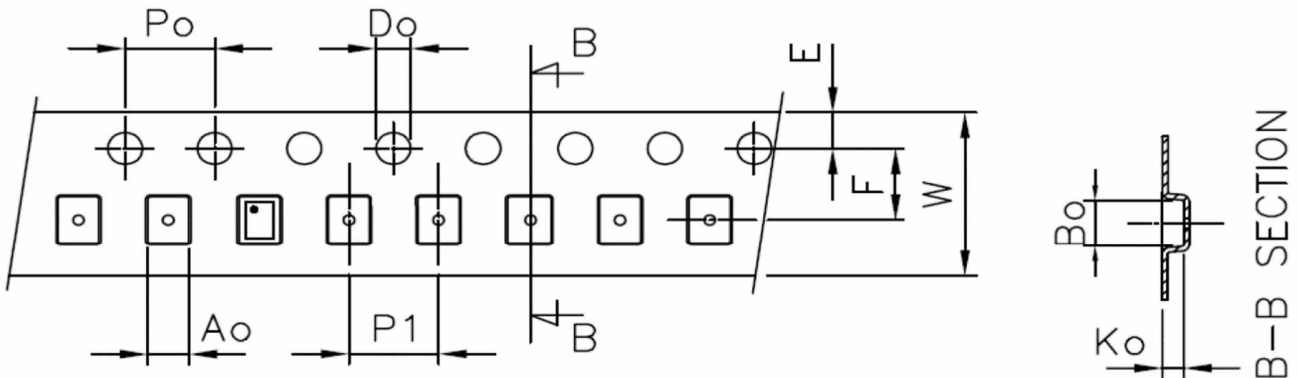


#### Tape and Reel Specification

Package Type	# of Pins	Nominal Package Size [mm]	Max Units		Reel & Hub Size [mm]	Leader (min)		Trailer (min)		Tape Width [mm]	Part Pitch [mm]
			per Reel	per Box		Pockets	Length [mm]	Pockets	Length [mm]		
STQFN 12L FCA 0.4P Green	12	1.6x1.6x0.55	3000	3000	178/60	100	400	100	400	8	4

#### Carrier Tape Drawing and Dimensions

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	B0	K0	P0	P1	D0	E	F	W
STQFN 12L FCA 0.4P Green	1.80±0.05	1.80±0.05	±0.7	4	4	1.5	1.75	3.5	8



#### Recommended Reflow Soldering Profile

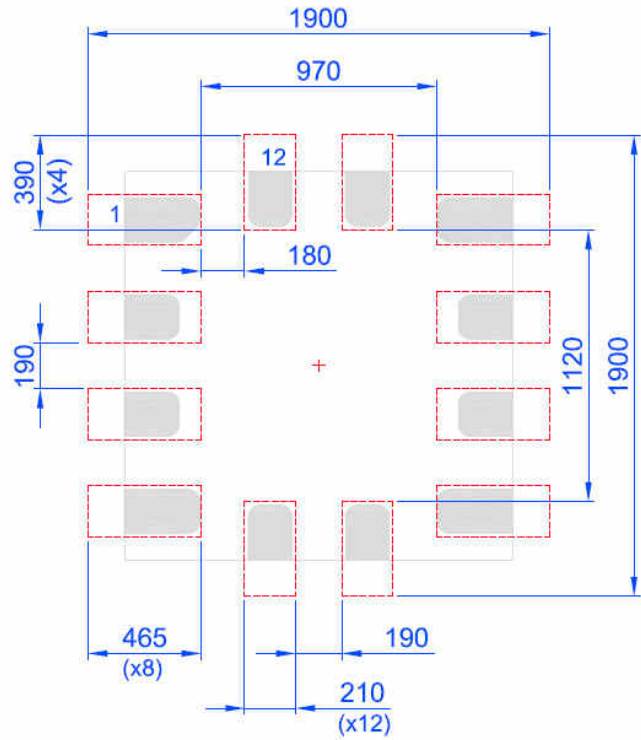
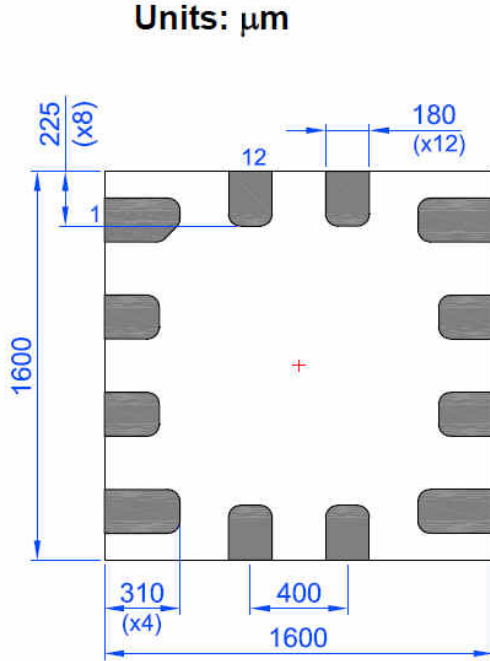
Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 1.408 mm<sup>3</sup> (nominal). More information can be found at [www.jedec.org](http://www.jedec.org).

#### Recommended Land Pattern

 Exposed Pad  
(PKG face down)

 Recommended Land Pattern  
(PKG face down)

Units:  $\mu\text{m}$



### Datasheet Revision History

Date	Version	Change
10/21/2021	0.10	New design
07/11/2023	0.11	Moved to Renesas template

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(Disclaimer Rev.1.01 Jan 2024)

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